

## Trench MOS Barrier Schottky Rectifier - 5Amp 60Volt

### Features

- For surface mounted applications
- Low profile package
- Built-in strain relief
- Metal silicon junction, majority carrier conduction
- Low power loss, high efficiency
- High current capability, low forward voltage drop
- High temperature soldering guaranteed
- High reliability
- High surge current capability
- Epitaxial construction
- Lead free device
- Halogen-Free

### Mechanical data

- Case : Molded plastic
- Epoxy : UL 94V-0 rate flame retardant
- Terminals : Solder plated, solderable per MIL-STD-750,method 2026
- Polarity : Color band denotes cathode end
- Weight : 0.003 ounce 0.0955 grams

### Maximum ratings and Electrical characteristics

Parameters	SBR5V6	UNIT
Maximum Recurrent Peak Reverse Voltage	60	V
Maximum RMS Voltage	42	V
Maximum DC Blocking Voltage	60	V
Maximum Average Forward Rectified Current	5	A
Peak Forward Surge Current	100	A
Maximum Instantaneous Forward Voltage at 5A	Tc = 25°C	V
	Tc = 125°C	
Maximum Average Reverse Current at Rated DC Blocking Voltage	Tc = 25°C	mA
	Tc = 125°C	
Typical Junction Capacitance	500	pF
Typical Thermal Resistance R <sub>θJL</sub> (Note 1)	18	°C/W
Operating and Storage Temperature Range	-50 to +150	°C

Note : 1. Mounted on P.C.B with copper pad size 14mm x 14mm

June 2015 / Rev.7.0

# SBR5V6

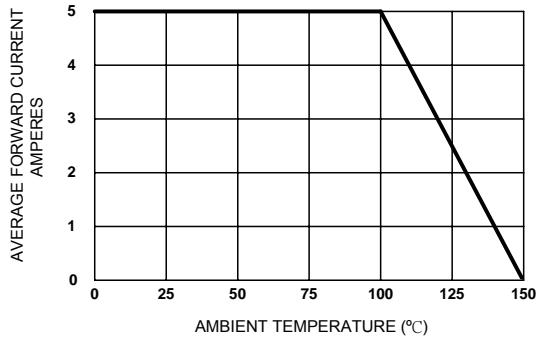


Figure 1. Forward Current Derating Curve

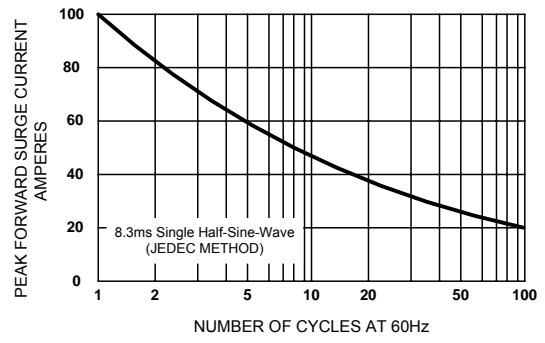


Figure 2. Maximum Non-repetitive Surge Current

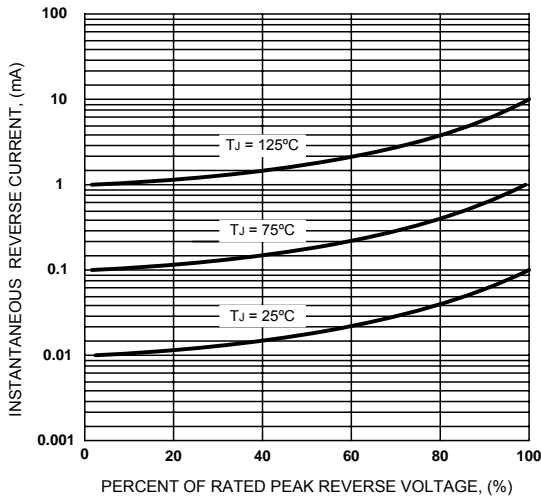


Figure 3. Typical Reverse Characteristics

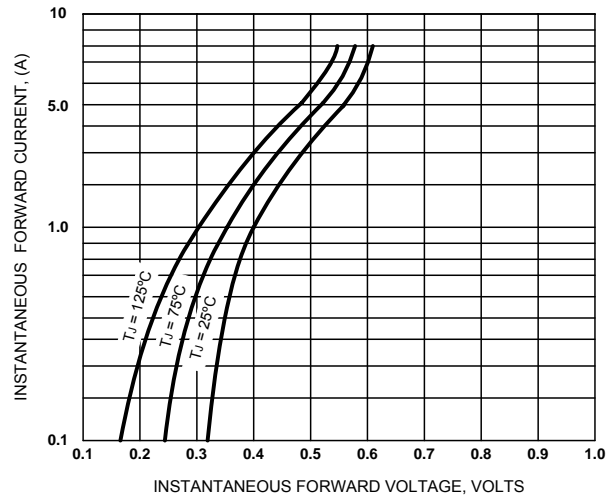


Figure 4. Typical Forward Characteristics

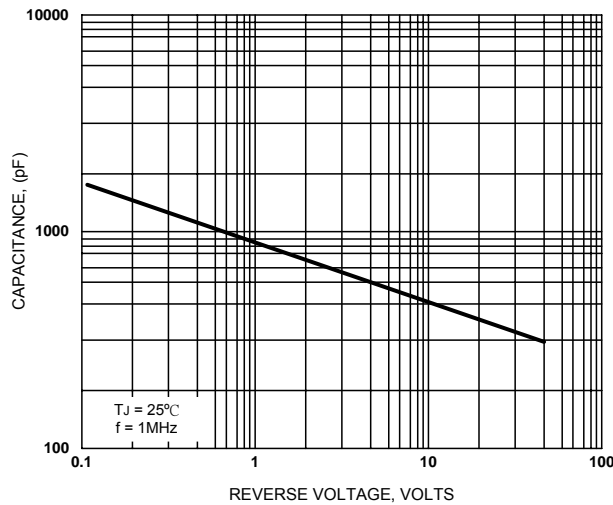


Figure 5. Typical Junction Capacitance



Sirectifier Semiconductor Inc.

U.S.A.: [sgc@sirect.com](mailto:sgc@sirect.com)

China: [st@sirect.com](mailto:st@sirect.com)

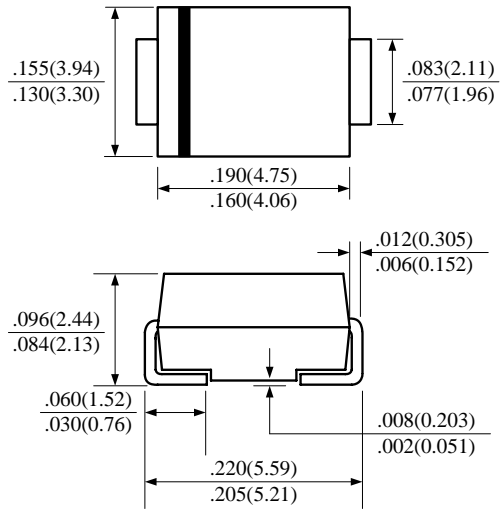
Taiwan: [se@sirect.com](mailto:se@sirect.com)

Hong Kong: [hk@sirect.com](mailto:hk@sirect.com)

<http://www.sirect.com>

SBR5V6

SMB



UNIT : inch(mm)

K ← | → A